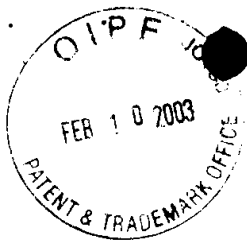


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PATENT

1765
#210
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(17)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Patent Application

Applicant: Kozo Nakamura, et al.

Serial No.: 09/856,212

Filed: May 18, 2001

For: Production Method For Silicon Single Crystal)
And Production Device For Single Crystal)
Ingot, And Heat Treating Method For Silicon)
Single Crystal Water)

) Group Art Unit: 1765

)

) I hereby certify that this correspondence

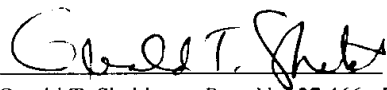
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) 20231, on February 4, 2003.

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) Gerald T. Shekleton Reg. No. 27,466 Date

Examiner: Matthew J. Song

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The Office Action of November 5, 2002 has been carefully reviewed and the following amendments/remarks are made in response thereto.

IN THE CLAIMS

Please amend Claims 1-5, 7 and 9-11 as follows:

1. (Amended) A method for producing a relatively defect free silicon single crystal ingot under the following conditions: